

Flat Gain, Ultra-Wideband

# Monolithic Amplifier

LVA-123+

50Ω 0.01 to 12 GHz



CASE STYLE: DQ849

## The Big Deal

- Ultra broadband performance
- Excellent Gain Flatness through 8 GHz
- Broadband without external matching components

## Product Overview

LVA-123+ (RoHS compliant) is an advanced ultra-wideband amplifier fabricated using GaAs HBT technology and offers excellent gain flatness over a broad frequency range. In addition, the LVA-123+ has good input and output return loss over this frequency range without the need for external matching components. Lead finish is tin-silver over nickel. It has repeatable performance from lot to lot and is enclosed in a 3x3 mm 8-lead package for very good thermal performance.

## Key Features

Feature	Advantages
Ultra Broad Band: 0.01 to 12 GHz	Broadband covering primary wireless communications bands: Cellular, PCS, LTE, WiMAX in a single amplifier.
Ultra Flat Gain ±0.6 dB typ. 0.05 - 6 GHz ±1.0 dB typ. 0.05 - 8 GHz	Ultra Flat Gain, eliminates need for compensation networks to achieve published results
Wideband Bias-Tee, TCBT-123+	Enables customer to realize full BW without changing any components
No External Matching Components Required	LVA-123+ provides good Input and Output Return Loss of 12-28 dB over 0.05 - 6 GHz without the need for any external matching components
Excellent ESD HBM: class 1C (1000 to <2000V) MM: class M2 (100 to <200V)	Simplifies ESD handling.



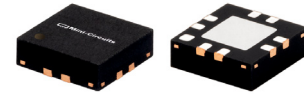
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# Monolithic Amplifier

0.01-12 GHz

## Product Features

- Excellent Gain Flatness,  $\pm 0.6$  dB, 0.05-6 GHz
- Gain, 17.3 dB typ. at 2 GHz
- Excellent input return loss, 20 dB typ., 2 GHz



Generic photo used for illustration purposes only

## LVA-123+

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## Typical Applications

- Base station infrastructure
- Test instruments
- MMDS & Wireless LAN
- LTE
- Satellite communication
- Avionics

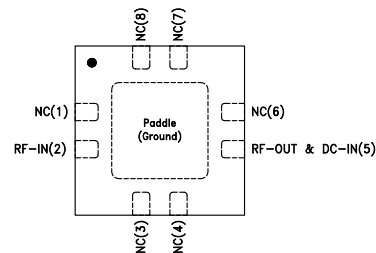
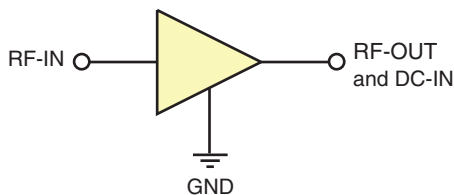
**+RoHS Compliant**

The +Suffix identifies RoHS Compliance. See our web site for RoHS Compliance methodologies and qualifications

## General Description

LVA-123+ (RoHS compliant) is an advanced ultra-wideband amplifier fabricated using GaAs HBT technology and offers excellent gain flatness over a broad frequency range. In addition, the LVA-123+ has good input and output return loss over this frequency range without the need for external matching components. Lead finish is tin-silver over nickel. It has repeatable performance from lot to lot and is enclosed in a 3x3 mm 8-lead package for very good thermal performance.

## simplified schematic and pin description



Function	Pin Number	Description
RF IN	2	RF input pin. This pin requires the use of an external DC blocking capacitor chosen for the frequency of operation.
RF-OUT and DC-IN	5	RF output and bias pin. DC voltage is present on this pin; therefore a DC blocking capacitor is necessary for proper operation. An RF choke is needed to feed DC bias without loss of RF signal due to the bias connection, as shown in "Recommended Application Circuit", Fig. 2
GND	Paddle	Connections to ground. Use via holes as shown in "Suggested Layout for PCB Design" to reduce ground path inductance for best performance.
NC	1,3,4,6,7,8	No connection

**Electrical Specifications<sup>1</sup> at 25°C and Vcc=5V, R= 16.5Ω unless noted**

Parameter	Condition (GHz)	Min.	Typ.	Max.	Units
Frequency range		0.01		12.0	GHz
Gain	0.05	—	16.5	—	dB
	0.85	—	17.4	—	
	2.0	15.6	17.3	19.0	
	6.0	—	16.7	—	
	8.0	—	14.7	—	
	10.0	—	11.6	—	
	12.0	—	8.1	—	
Gain flatness	0.05-6		±0.6		dB
Input return loss	0.05	—	13.7	—	dB
	0.85	—	25.0	—	
	2.0	16.0	25.0	—	
	6.0	—	18.3	—	
	8.0	—	9.7	—	
	10.0	—	6.9	—	
Output return loss	0.05		13.5		dB
	0.85		21.3		
	2.0		16.5		
	6.0		11.6		
	8.0		7.1		
	10.0		6.2		
Reverse isolation	6.0		19.2		dB
Output power at 1dB compression	0.05		17.2		dBm
	0.85		16.5		
	2.0		15.6		
	6.0		13.3		
	8.0		10.8		
	10.0		7.8		
Output IP3	0.2		29.0		dBm
	0.85		30.3		
	2.0		28.2		
	6.0		23.6		
	8.0		22.1		
	10.0		18.5		
Noise figure	0.2		3.7		dB
	0.85		3.7		
	2.0		3.9		
	6.0		4.1		
	8.0		4.4		
	10.0		5.2		
Supply operating voltage (Vcc)		4.8	5.0	5.2	V
Device operating current		—	52	57	mA
Device current variation vs. temperature <sup>2</sup>			59		μA/°C
Device current variation vs. voltage			0.019		mA/mV
Thermal resistance, junction-to-ground lead			156		°C/W

1. Measured on Mini-Circuits Characterization test board TB-841+. See Characterization Test Circuit (Fig. 1)

2. (Current at 85°C — Current at -45°C)/130

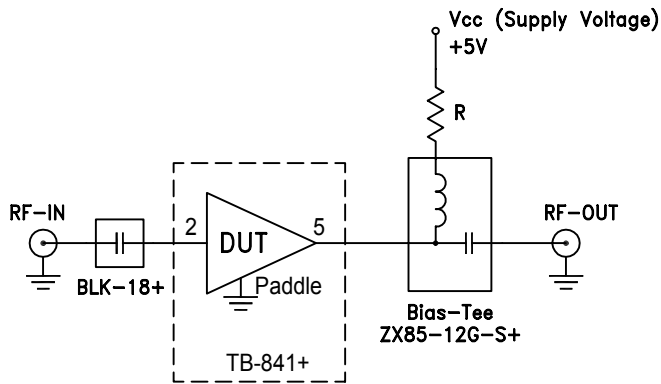
**Absolute Maximum Ratings<sup>3</sup>**

Parameter	Ratings
Operating temperature (ground lead)	-40°C to 85°C
Storage temperature	-65°C to 150°C
Operating current at 5V (Vcc) & 16.5Ω resistor	100 mA
Power dissipation	0.34 W
Input power (CW)	28 dBm (5 min max.) 11 dBm (continuous)
DC voltage on Pad 5	6 V

3. Permanent damage may occur if any of these limits are exceeded.  
Electrical maximum ratings are not intended for continuous normal operation.



### Characterization Test Circuit

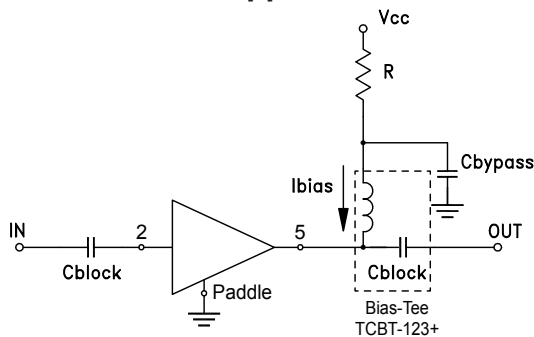


**Fig 1.** Block Diagram of Test Circuit used for characterization. (DUT soldered on Mini-Circuits Characterization test board TB-841+) Gain, Return loss, Output power at 1dB compression (P1 dB) , output IP3 (OIP3) and noise figure measured using Agilent’s N5242A PNA-X microwave network analyzer. (R=16.5Ω)

**Conditions:**

1. Gain and Return loss: Pin= -25dBm
2. Output IP3 (OIP3): Two tones, spaced 1 MHz apart, 0 dBm/tone at output.

### Recommended Application Circuit



**Fig 2.** Test Board includes case, connectors, and components soldered to PCB (Cblock=0.001 μF, Cbypass=0.1 μF, R=16.5Ω)

### Product Marking

